



Patent  
Attorney's Docket No. 001425-104

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of )

Masahiko TANAKA et al. )

Application No.: 09/862,458 )

Filed: May 23, 2001 )

For: THIN-FILM DISPOSITION  
APPARATUS )

Group Art Unit: 1763

Examiner: Karla A. Moore

Confirmation No.: 7476

#5A  
2/11/03  
KW

**AMENDMENT**

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

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FEB 10 2003  
TC 1700 MAIL ROOM

In response to the Official Action dated November 6, 2002, please amend the  
above-identified patent application as follows:

**IN THE SPECIFICATION:**

Please replace paragraphs 25 and 54 as follows:

A<sub>1</sub>  
[0025] In the above-mentioned thin-film deposition apparatus according to the present invention, the above-mentioned plurality of holes through which the radicals pass are preferably formed so as to satisfy the condition  $uL/D > 1$ , where  $u$  is the gas flow rate inside these holes,  $L$  is the effective length of the holes (in the embodiments shown in Figures 2, 3 and 4, this length is equivalent to the thickness of dividing plate 24), and  $D$  is the gas interdiffusion coefficient (the gas interdiffusion coefficient of the precursor gas and the gas introduced in the plasma discharge space at the holes). In a thin-film deposition